

High-speed Switching Transistor (-60V, -12A)

2SA1870

●Features

- 1) High speed switching, typically $t_f = 0.17 \mu s$ at $I_C = -6A$.
- 2) Low saturation voltage, typically $V_{CE(sat)} = -0.2V$ at $I_C / I_E = -6A / -0.3A$.
- 3) Wide SOA (safe operating area)

●Packaging specifications and hFE

Type	2SA1870
Package	PSD3
h_{FE}	EF
Code	TL
Basic ordering unit (pieces)	1000

●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-100	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-12 -20	A (Pulse) *
Collector power dissipation	P_C	1.5 35	W ($T_c = 25^\circ C$)
Junction temperature	T_J	150	°C
Storage temperature	T_{STG}	-55 ~ +150	°C

* Single pulse, $P_w = 100\text{ms}$ **●Electrical characteristics ($T_a = 25^\circ C$)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-100	—	—	V	$I_C = -50 \mu A$
Collector-emitter breakdown voltage	$BV_{CEO(SUS)}$	-60	—	—	V	$I_C = -6A, I_E = -0.6A, L = 1mH$
Collector-emitter breakdown voltage	BV_{CEO}	-60	—	—	V	$I_C = -1mA$
Emitter-base breakdown voltage	BV_{EBO}	-5	—	—	V	$I_E = -50 \mu A$
Collector cutoff current	I_{CB0}	—	—	-10	μA	$V_{CB} = -100V$
Emitter cutoff current	I_{EB0}	—	—	-10	μA	$V_{EB} = -5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	-0.2	-0.3	V	$I_C/I_E = -6A/-0.3A$
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	-0.5	V	$I_C/I_E = -8A/-0.4A$
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	-1.2	V	$I_C/I_E = -6A/-0.3A$
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	-1.5	V	$I_C/I_E = -8A/-0.4A$
DC current transfer ratio	h_{FE}	100	—	320	—	$V_{CE} = -2V, I_C = -2A$
Transition frequency	f_T	—	80	—	MHz	$V_{CB} = -10V, I_E = -1A, f = 30MHz$
Output capacitance	C_{OB}	—	250	—	pF	$V_{CE} = -10V, I_E = 0A, f = 1MHz$
Turn-on time	t_{on}	—	—	0.3	μs	$I_C = -6A$
Storage time	t_{STG}	—	—	1.5	μs	$I_{S1} = -I_{S2} = -0.3A$
Fall time	t_f	—	0.17	0.3	μs	$V_{CC} \sim -30V$

(96-113-A325)